BLF183XR; BLF183XRS

Power LDMOS transistor Rev. 3 — 1 September 2015

AMPLEON

Product data sheet

Product profile 1.

1.1 General description

A 350 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 600 MHz band.

Table 1. **Application information**

Test signal	f	V _{DS}	PL	Gp	η _D
	(MHz)	(V)	(W)	(dB)	(%)
pulsed RF	108	50	350	28	75
CW	88 to 108	50	388	26	80
pulsed RF	30 to 512	50	400	15	48
CW	30 to 512	35	193	14	47

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (HF to 600 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified out	line Graphic symbol
BLF183X	R (SOT1121A)		
1	drain1		
2	drain2	1 2 M M	1
3	gate1	5	
4	gate2		5
5	source	[1] 3 4	4 7
			<u>"</u>
			2 sym117
BLF183X	RS (SOT1121B)		
1	drain1	F3 F3	
2	drain2	[1] [2]	_
3	gate1		
4	gate2	3 4	5 3 - 5
5	source	[1]	4 —
			' <u></u>
			2 sym117

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package			
	Name	Description	Version		
BLF183XR	-	flanged LDMOST ceramic package; 2 mounting holes; 4 leads	SOT1121A		
BLF183XRS	-	earless flanged ceramic package; 4 leads	SOT1121B		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	135	٧
V_{GS}	gate-source voltage		-6	+11	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

 Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

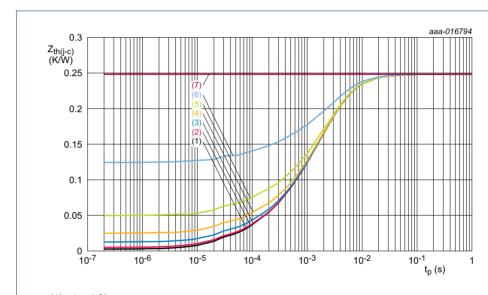
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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _j = 115 °C	[1][2]	0.25	K/W
Z _{th(j-c)}	transient thermal impedance from junction to case	T_j = 150 °C; t_p = 100 μs; δ = 20 %	[3]	0.076	K/W

- [1] T_i is the junction temperature.
- [2] $R_{th(j-c)}$ is measured under RF conditions.
- [3] See Figure 1.



- (1) $\delta = 1 \%$
- (2) $\delta = 2 \%$
- (3) $\delta = 5 \%$
- (4) $\delta = 10 \%$
- (5) $\delta = 20 \%$
- (6) $\delta = 50 \%$
- (7) $\delta = 100 \% (DC)$

Fig 1. Transient thermal impedance from junction to case as a function of pulse duration

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.5 \text{ mA}$	135	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 150 mA	1.33	2.0	2.33	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 50 \text{ mA}$	-	1.9	-	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	1.4	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	21	-	А
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.25 \text{ A}$	-	0.29	-	Ω

Table 7. AC characteristics

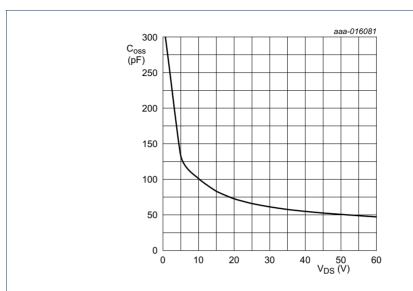
 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{rs}	feedback capacitance	V _{GS} = 0 V; V _{DS} = 50 V; f = 1 MHz	-	1.1	-	pF
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 50 V; f = 1 MHz	-	156	-	pF
C _{oss}	output capacitance	V _{GS} = 0 V; V _{DS} = 50 V; f = 1 MHz	-	51	-	pF

Table 8. RF characteristics

Test signal: pulsed RF; t_p = 100 μ s; δ = 20 %; f = 108 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 100 mA; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	P _L = 350 W	26.5	28	-	dB
RLin	input return loss	P _L = 350 W	-	-10	-7	dB
η_{D}	drain efficiency	P _L = 350 W	71	75	-	%



 $V_{GS} = 0 V$; f = 1 MHz.

Fig 2. Output capacitance as a function of drain-source voltage; typical values per section

7. Test information

7.1 Ruggedness in class-AB operation

The BLF183XR and BLF183XRS are capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions: $V_{DS} = 50 \text{ V}$; $I_{Dq} = 100 \text{ mA}$; $P_L = 350 \text{ W}$ pulsed; f = 108 MHz.

7.2 Impedance information

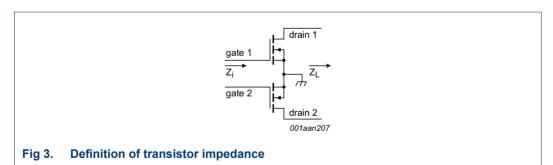


Table 9. Typical push-pull impedance

Simulated Z_i and Z_L device impedance; impedance info at $V_{DS} = 50 \text{ V}$ and $P_L = 350 \text{ W}$.

f	Z _i	Z _L
(MHz)	(Ω)	(Ω)
108	10.3 – j35.6	10.9 + j2.5

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7.3 UIS avalanche energy

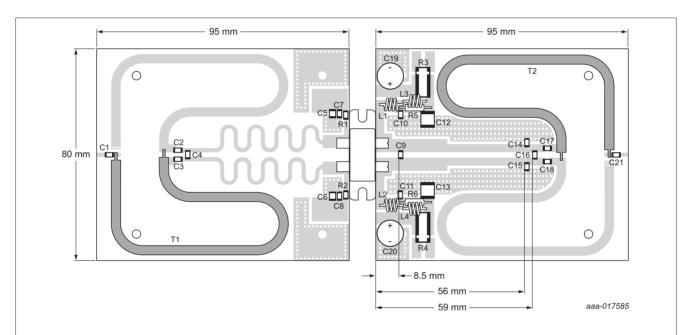
Table 10. Typical avalanche data per section

 $T_{amb} = 25$ °C; typical test data; test jig without water cooling.

IAS	E _{AS}
(A)	(J)
10	2.6
12.5	1.5
15	1.0

For information see application note AN10273.

7.4 Test circuit



Printed-Circuit Board (PCB): Taconic RF-35; ϵ_r = 3.5 F/m; thickness = 0.765 mm; thickness copper plating = 35 μ m, gold plated.

See Table 11 for a list of components.

Fig 4. Component layout for class-AB production test circuit

Table 11. List of components For test circuit see Figure 4.

Component	Description	Value	Remarks
C1, C4	multilayer ceramic chip capacitor	51 pF [1]	
C2, C3	multilayer ceramic chip capacitor	150 pF [1]	
C5, C6	multilayer ceramic chip capacitor	4.7 μF, 50 V	
C7, C8	multilayer ceramic chip capacitor	820 pF [1]	
C9	multilayer ceramic chip capacitor	11 pF [1]	
C10, C11	multilayer ceramic chip capacitor	820 pF [1]	
C12, C13	multilayer ceramic chip capacitor	4.7 μF, 100 V	
C14, C15, C21	electrolytic capacitor	51 pF [1]	

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 Table 11.
 List of components ...continued

For test circuit see Figure 4.

Component	Description	Value	Remarks
C16	multilayer ceramic chip capacitor	7.5 pF [1]	
C17,C18	multilayer ceramic chip capacitor	120 pF [1]	
C19, C20	electrolytic capacitor	2200 μF, 64 V	
L1, L2, L3, L4	3.0 turn 1.0 mm copper wire	D = 3.0 mm	
R1, R2	resistor	510 Ω	SMD 1206
R3, R4	shunt resistor	0.01 Ω	Ohmite: FC4L110R010FER
R5, R6	metal film resistor	10 Ω, 0.6 W	SMD 1206
T1, T2	semi rigid coax	50Ω , length = 160 mm	EZ Form: EZ-141-AL-TP-M17

^[1] American Technical Ceramics type 100B or capacitor of same quality.

7.5 Graphical data

The following figures are measured in a class-AB production test circuit.

7.5.1 1-Tone CW pulsed

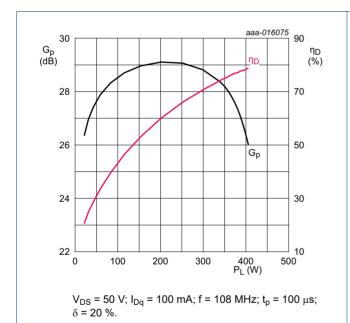
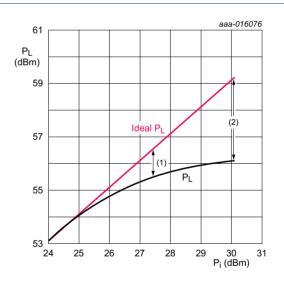


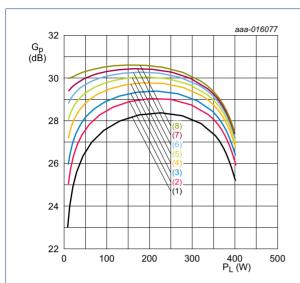
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 50 V; I_{Dq} = 100 mA; f = 108 MHz; t_p = 100 μs ; δ = 20 %.

- (1) $P_{L(1dB)} = 55.5 \text{ dBm } (354 \text{ W})$
- (2) $P_{L(3dB)} = 56.1 \text{ dBm } (404 \text{ W})$

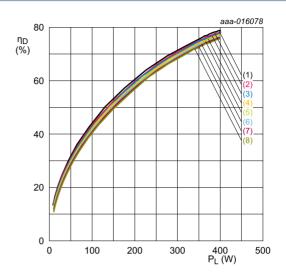
Fig 6. Output power as a function of input power; typical values



 V_{DS} = 50 V; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 20 \text{ mA}$
- (2) $I_{Dq} = 100 \text{ mA}$
- (3) $I_{Dq} = 200 \text{ mA}$
- (4) $I_{Dq} = 400 \text{ mA}$
- (5) $I_{Dq} = 600 \text{ mA}$
- (6) $I_{Dq} = 800 \text{ mA}$
- (7) $I_{Dq} = 1000 \text{ mA}$
- (8) $I_{Dq} = 1200 \text{ mA}$

Fig 7. Power gain as a function of output power; typical values



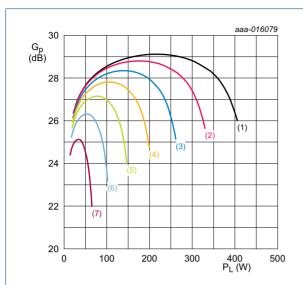
 V_{DS} = 50 V; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $I_{Dq} = 20 \text{ mA}$
- (2) $I_{Dq} = 100 \text{ mA}$
- (3) $I_{Dq} = 200 \text{ mA}$
- (4) $I_{Dq} = 400 \text{ mA}$
- (5) $I_{Dq} = 600 \text{ mA}$
- (6) $I_{Dq} = 800 \text{ mA}$
- (7) $I_{Dq} = 1000 \text{ mA}$
- (8) $I_{Dq} = 1200 \text{ mA}$

Fig 8. Drain efficiency as a function of output power; typical values

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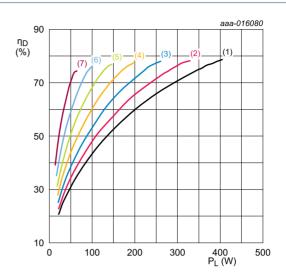
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 I_{Dq} = 100 mA; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$
- (6) $V_{DS} = 25 \text{ V}$
- (7) $V_{DS} = 20 \text{ V}$

Fig 9. Power gain as a function of output power; typical values



 I_{Dq} = 100 mA; f = 108 MHz; t_p = 100 μ s; δ = 20 %.

- (1) $V_{DS} = 50 \text{ V}$
- (2) $V_{DS} = 45 \text{ V}$
- (3) $V_{DS} = 40 \text{ V}$
- (4) $V_{DS} = 35 \text{ V}$
- (5) $V_{DS} = 30 \text{ V}$ (6) $V_{DS} = 25 V$
- (7) $V_{DS} = 20 \text{ V}$

Fig 10. Drain efficiency as a function of output power; typical values

8. Package outline

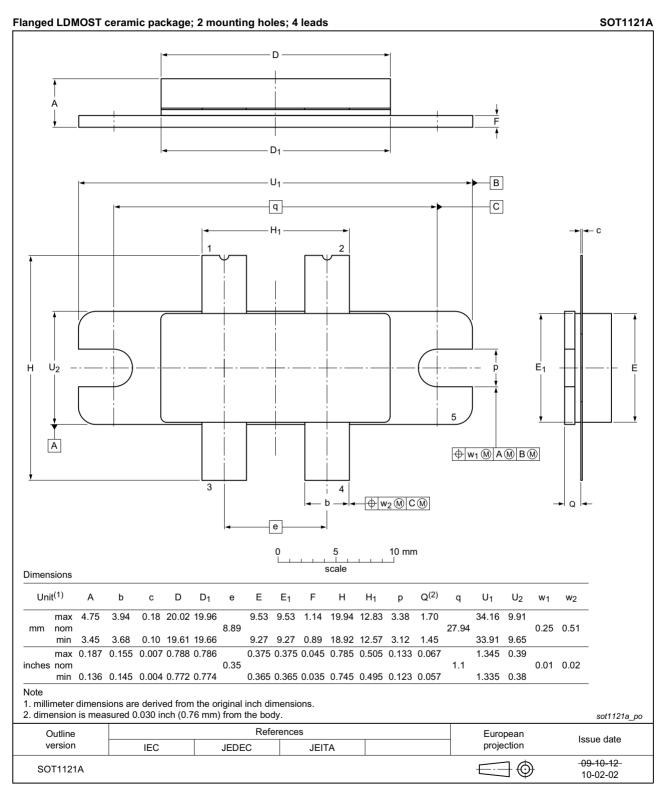


Fig 11. Package outline SOT1121A

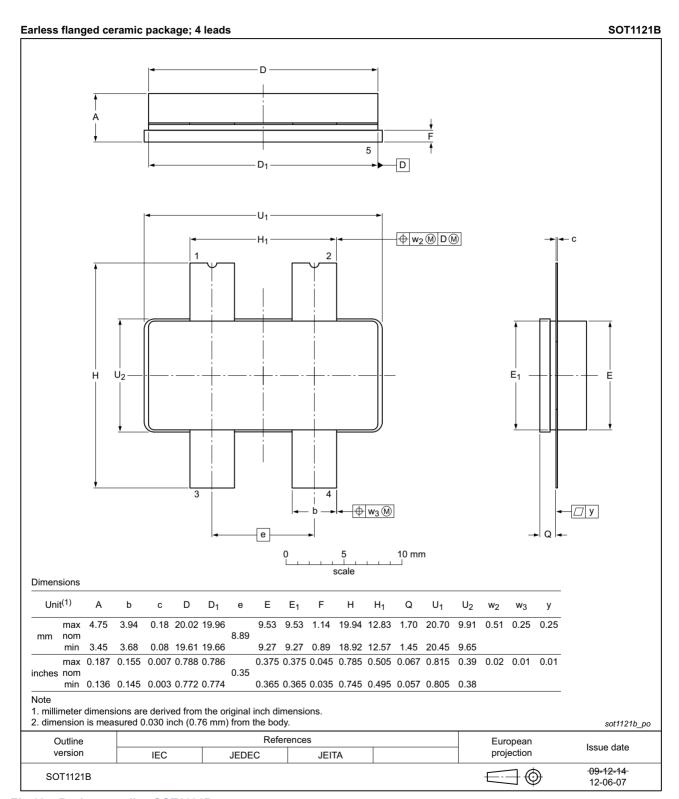


Fig 12. Package outline SOT1121B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 12. Abbreviations

Acronym	Description
CW	Continuous Wave
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
MTF	Median Time to Failure
SMD	Surface Mounted Device
UIS	Unclamped Inductive Switching
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF183XR_BLF183XRS#3	20150901	Product data sheet	-	BLF183XR_BLF183XRS v.2	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLF183XR_BLF183XRS v.2	20150522	Product data sheet	-	BLF183XR_BLF183XRS v.1	
BLF183XR_BLF183XRS v.1	20140819	Objective data sheet	-	-	

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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